

TOSHIBA Photocoupler GaAs IRed & Photo-Transistor

TLP531, TLP532

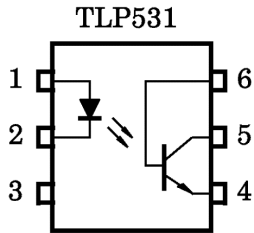
Programmable Controllers
 AC / DC-Input Module
 Solid State Relay

The TOSHIBA TLP531 and TLP532 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

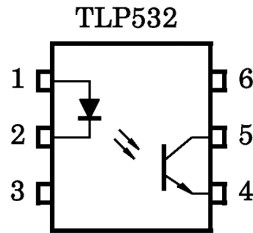
TLP532 is no-base internal connection for high-EMI environments.

- Collector-emitter voltage: 55 V (min.)
- Current transfer ratio: 50% (min.)
 Rank GB: 100% (min.)
- Isolation voltage: 2500 V_{rms} (min.)
- UL recognized: UL1577, file no. E67349

Pin Configurations (top view)

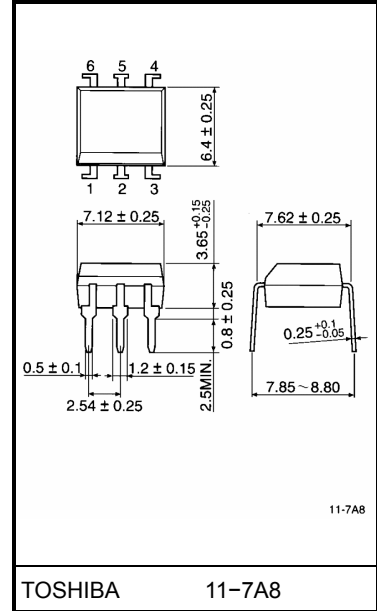


- TLP531**
- 1 : ANODE
 - 2 : CATHODE
 - 3 : N.C.
 - 4 : EMITTER
 - 5 : COLLECTOR
 - 6 : BASE



- TLP532**
- 1 : ANODE
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Unit in mm



Weight: 0.4g

Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | | Symbol | Rating | Unit |
|--|---|-------------------------------|---------|-----------|
| LED | Forward current | I_F | 70 | mA |
| | Forward current derating (Ta ≥ 50°C) | $\Delta I_F / ^\circ\text{C}$ | 0.93 | mA / °C |
| | Peak forward current (100 μs pulse, 100pps) | I_{FP} | 1 | A |
| | Reverse voltage | V_R | 5 | V |
| | Junction temperature | T_j | 125 | °C |
| Detector | Collector-emitter voltage | V_{CEO} | 55 | V |
| | Collector-base voltage (TLP531) | V_{CBO} | 80 | V |
| | Emitter-collector voltage | V_{ECO} | 7 | V |
| | Emitter-base voltage (TLP531) | V_{EBO} | 7 | V |
| | Collector current | I_C | 50 | mA |
| | Power dissipation | P_C | 150 | mW |
| | Power dissipation derating (Ta ≥ 25°C) | $\Delta P_C / ^\circ\text{C}$ | -1.5 | mW / °C |
| | Junction temperature | T_j | 125 | °C |
| Storage temperature range | | T_{stg} | -55~125 | °C |
| Operating temperature range | | T_{opr} | -55~100 | °C |
| Lead soldering temperature (10s) | | T_{sol} | 260 | °C |
| Total package power dissipation | | P_T | 250 | mW |
| Total package power dissipation derating (Ta ≥ 25°C) | | $\Delta P_T / ^\circ\text{C}$ | -2.5 | mW / °C |
| Isolation voltage (AC, 1min., R.H.≤ 60%) | | BV_S | 2500 | V_{rms} |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Recommends Operating Conditions

| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|-----------------------|-----------|------|------|------|------|
| Supply voltage | V_{CC} | — | 5 | 24 | V |
| Forward current | I_F | — | 16 | 25 | mA |
| Collector current | I_C | — | 1 | 10 | mA |
| Operating temperature | T_{opr} | -25 | — | 85 | °C |

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

| Characteristic | | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|------------------------------------|---|--------------------------|---|------|------|------|---------------|
| LED | Forward voltage | V_F | $I_F = 10\text{mA}$ | 1.0 | 1.15 | 1.3 | V |
| | Reverse current | I_R | $V_R = 5\text{V}$ | — | — | 10 | μA |
| | Capacitance | C_T | $V = 0, f = 1\text{MHz}$ | — | 30 | — | pF |
| Detector | Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C = 0.5\text{mA}$ | 55 | — | — | V |
| | Emitter-collector breakdown voltage | $V_{(BR)ECO}$ | $I_E = 0.1\text{mA}$ | 7 | — | — | V |
| | Collector-base breakdown voltage (TLP531) | $V_{(BR)CBO}$ | $I_C = 0.1\text{mA}$ | 80 | — | — | V |
| | Emitter-base breakdown voltage (TLP531) | $V_{(BR)EBO}$ | $I_E = 0.1\text{mA}$ | 7 | — | — | V |
| | Collector dark current | I_{CEO} | $V_{CE} = 24\text{V}$ | — | 10 | 100 | nA |
| | | | $V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$ | — | 2 | 50 | μA |
| Capacitance (collector to emitter) | C_{CE} | $V = 0, f = 1\text{MHz}$ | — | 10 | — | pF | |

Coupled Electrical Characteristics (Ta = 25°C)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|--------------------------------------|---------------|--|------|------|------|------|
| Current transfer ratio | I_C / I_F | $I_F = 5\text{mA}, V_{CE} = 5\text{V}$ | 50 | 200 | 600 | % |
| | | Rank Y | 50 | — | 150 | |
| | | Rank YG | 50 | — | 300 | |
| | | Rank GR | 100 | — | 300 | |
| | | Rank GB | 100 | — | 600 | |
| | | Rank BL | 200 | — | 600 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 2.4\text{mA}, I_F = 8\text{mA}$ | — | — | 0.4 | V |

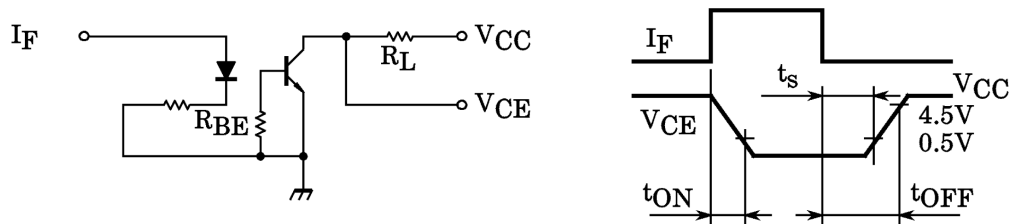
Isolation Characteristics (Ta = 25°C)

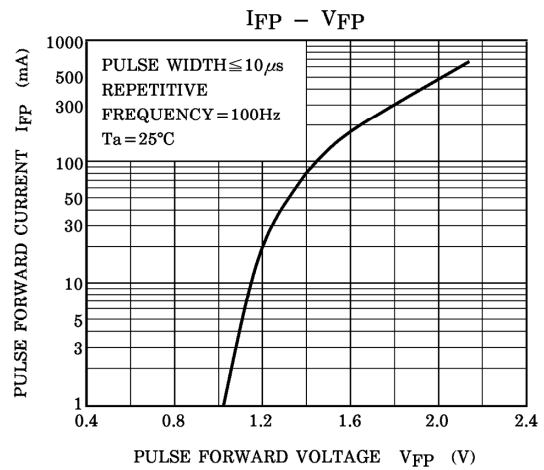
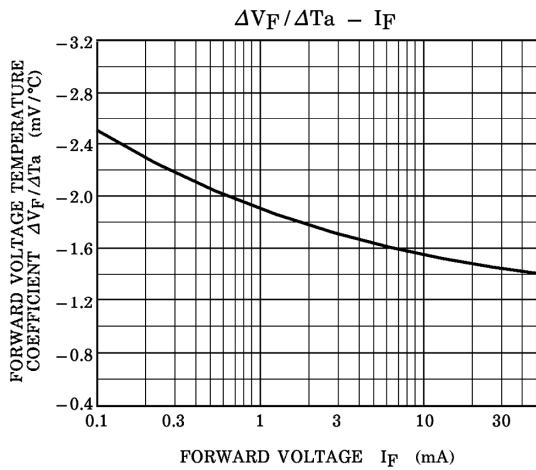
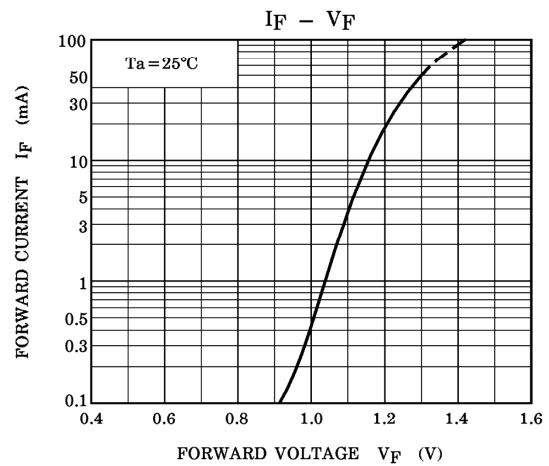
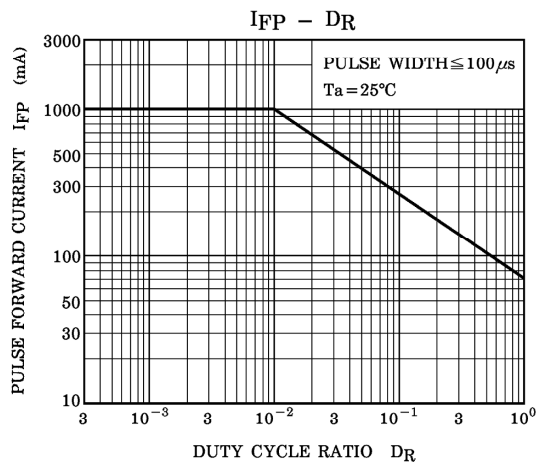
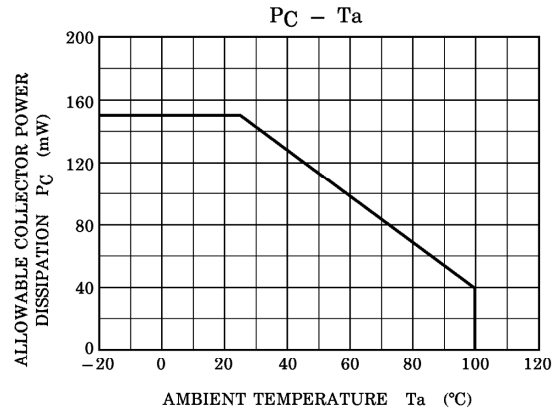
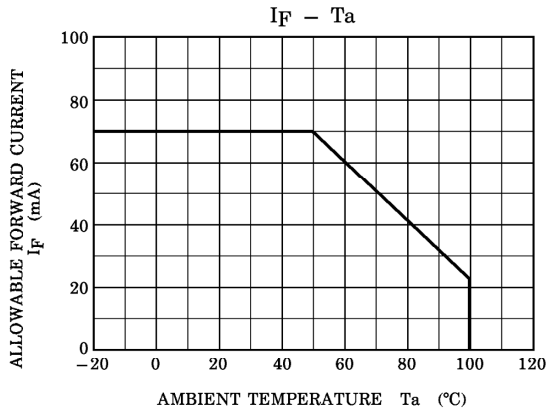
| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|-------------------------------|-----------------|-----------------------------------|----------------------|------------------|------|------------------|
| Capacitance (input to output) | C _S | V _S = 0, f = 1MHz | — | 0.8 | — | pF |
| Isolation resistance | R _S | V _S = 500V, R.H. ≤ 60% | 5 × 10 ¹⁰ | 10 ¹⁴ | — | Ω |
| Isolation voltage | BV _S | AC, 1 minute | 2500 | — | — | V _{rms} |

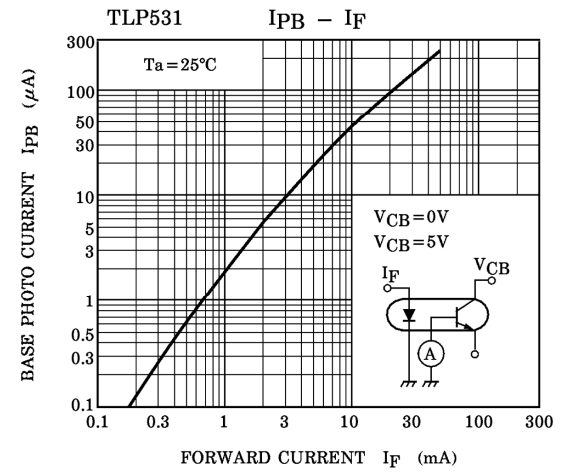
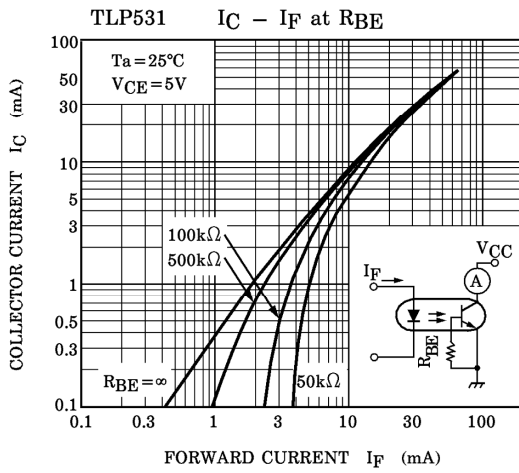
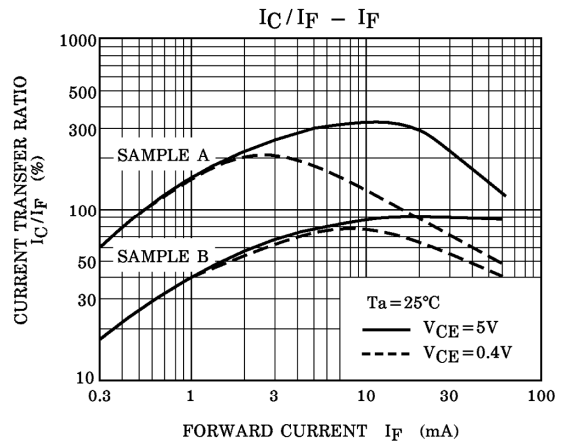
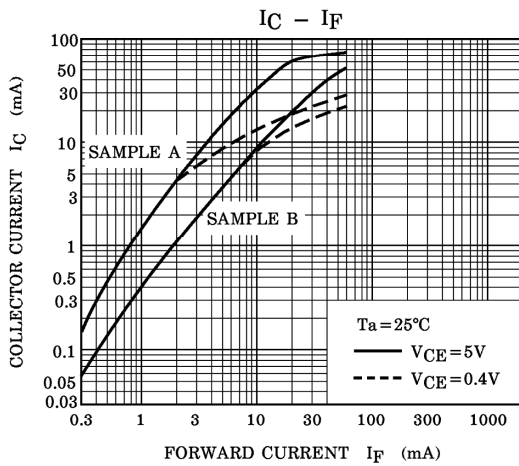
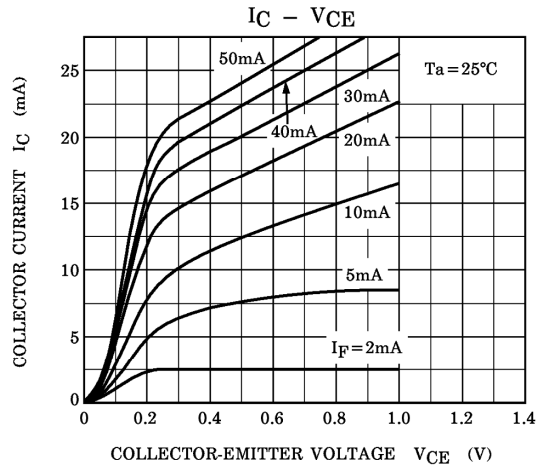
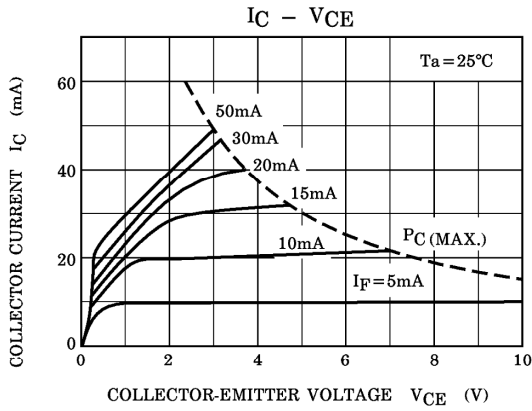
Switching Characteristics (Ta = 25°C)

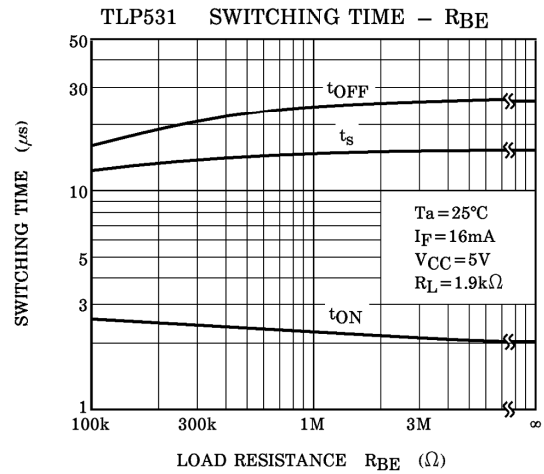
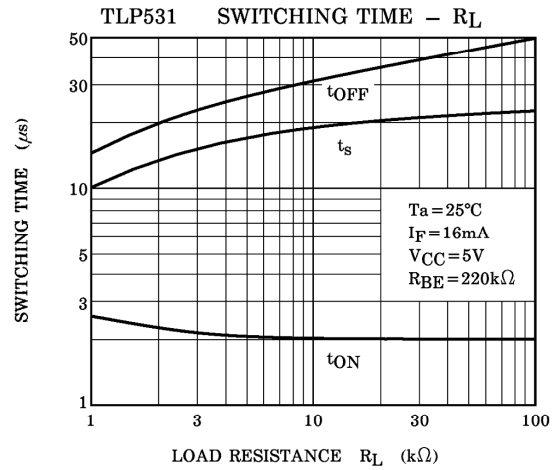
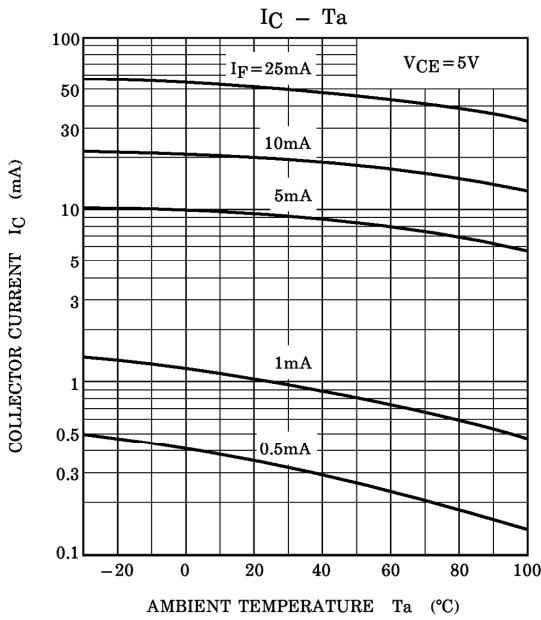
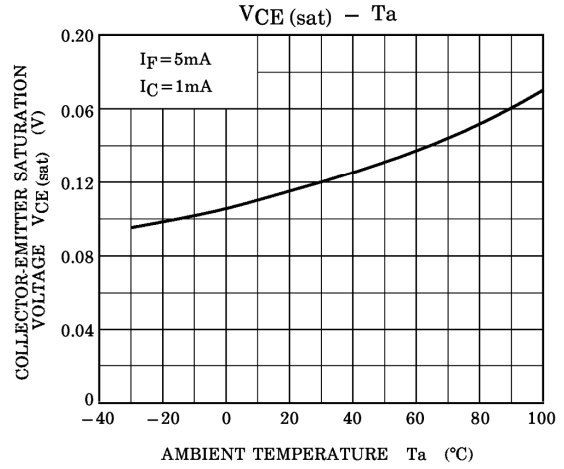
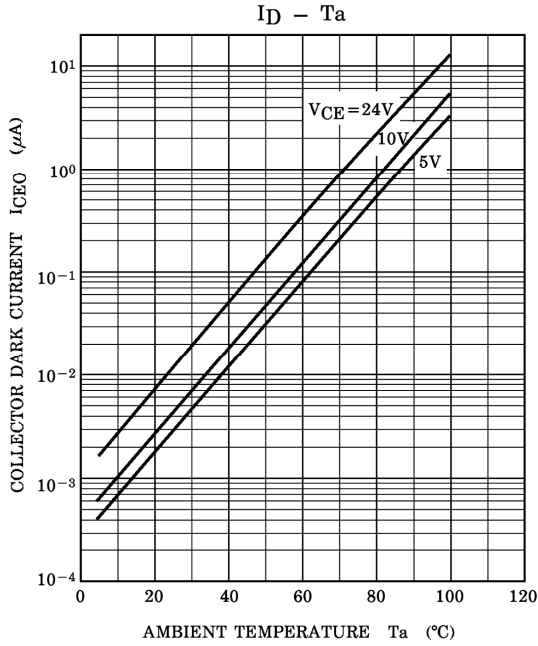
| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|----------------|------------------|---|------|------|------|------|
| Rise time | t _r | V _{CC} = 10V I _C = 2mA R _L = 100Ω | — | 2 | — | μs |
| Fall time | t _f | | — | 3 | — | |
| Turn-on time | t _{ON} | | — | 3 | — | |
| Turn-off time | t _{OFF} | | — | 3 | — | |
| Turn-on time | t _{ON} | R _L = 1.9kΩ R _{BE} = open V _{CC} = 5V, I _F = 16mA (Fig.1) | — | 2 | — | μs |
| Storage time | t _s | | — | 15 | — | |
| Turn-off time | t _{OFF} | | — | 25 | — | |
| Turn-on time | t _{ON} | R _L = 1.9Ω R _{BE} = 220kΩ (TLP531) V _{CC} = 5V, I _F = 16mA (Fig.1) | — | 2 | — | μs |
| Storage time | t _s | | — | 12 | — | |
| Turn-off time | t _{OFF} | | — | 20 | — | |

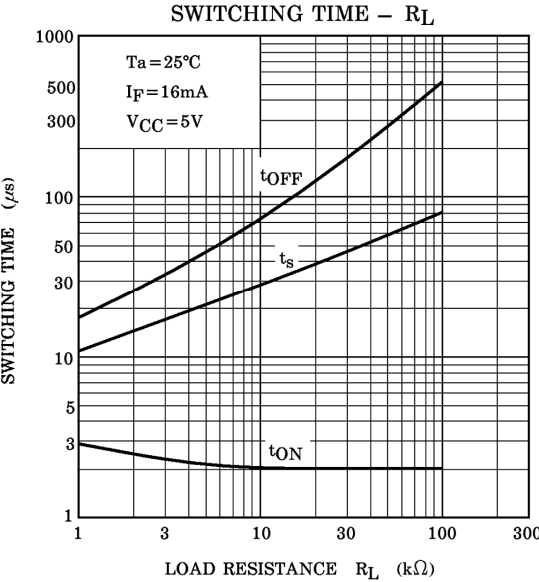
Fig. 1 Switching time test circuit











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